XBS206S17R-G

TOREX

ETR1613-002a

Schottky Barrier Diode, 2A, 60V Type

■FEATURES

Forward Voltage : V_F=0.615V (TYP.)
Forward Current : $I_{F(AVE)}$=2A
Repetitive Peak Reverse Voltage : V_{RM}=60V

■APPLICATIONS

●Rectification
●Protection against reverse connection of battery

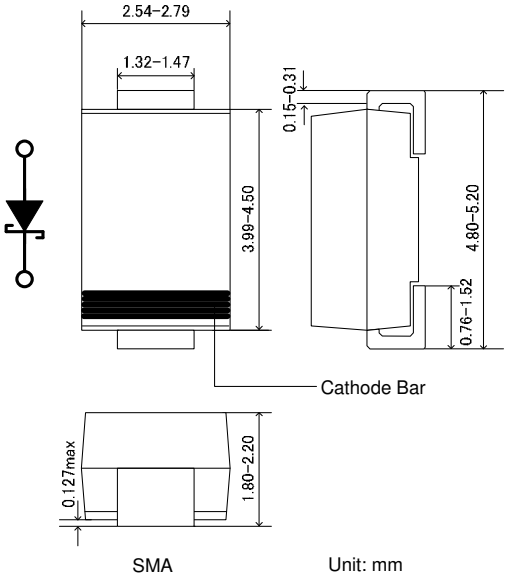
■ABSOLUTE MAXIMUM RATINGS

Ta=25℃

PARAMETER	SYMBOL	RATINGS	UNIT
Repetitive Peak Reverse Voltage	V_{RM}	60	V
Reverse Voltage (DC)	V_R	60	V
Forward Current (Average)	$I_{F(AVE)}$	2	A
Non Continuous Forward Surge Current*1	I_{FSM}	45	A
Junction Temperature	Tj	125	℃
Storage Temperature Range	Tstg	-55～+150	℃

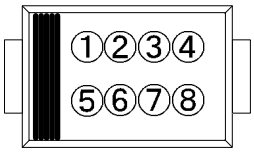
*1 : Non continuous high amplitude 60Hz half-sine wave.

■PACKAGING INFORMATION



SMA Unit: mm

■MARKING RULE



①②③④⑤⑥: 206S17(Product Number)
⑦⑧ : Assembly Lot Number

■PRODUCT NAME

PRODUCT NAME	DEVICE ORIENTATION
XBS206S17R-G	SMA (Halogen & Antimony free)
XBS206S17R	SMA

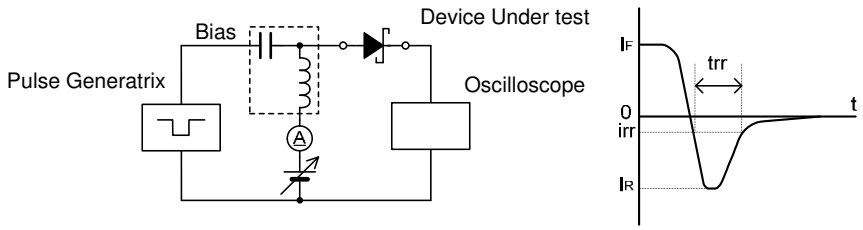
* The "-G" suffix indicates that the products are Halogen and Antimony free as well as being fully RoHS compliant.
* The device orientation is fixed in its embossed tape pocket.

■ELECTRICAL CHARACTERISTICS

Ta=25℃

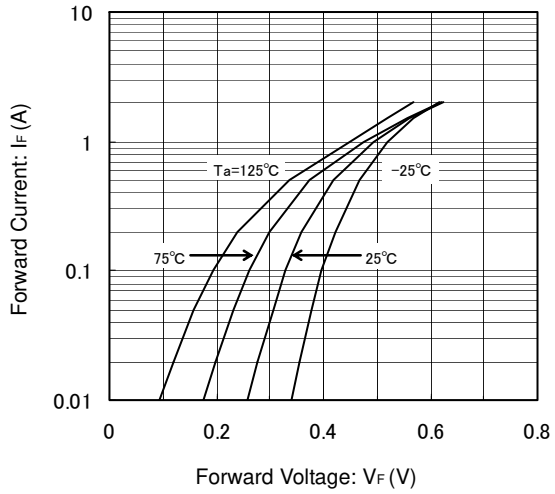
PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN.	TYP.	MAX.	
Forward Voltage	V_{F1}	I_F=200μA	-	0.15	-	V
	V_{F2}	I_F=2A	-	0.615	0.665	V
Reverse Current	I_{R1}	V_R=30V	-	2.5	-	μA
	I_{R2}	V_R=60V	-	10	300	μA
Inter-Terminal Capacity	Ct	V_R=1V , f=1MHz	-	120	-	pF
Reverse Recovery Time*2	trr	I_F=I_R=10mA , irr=1mA	-	35	-	ns

*2 : trr measurement circuit

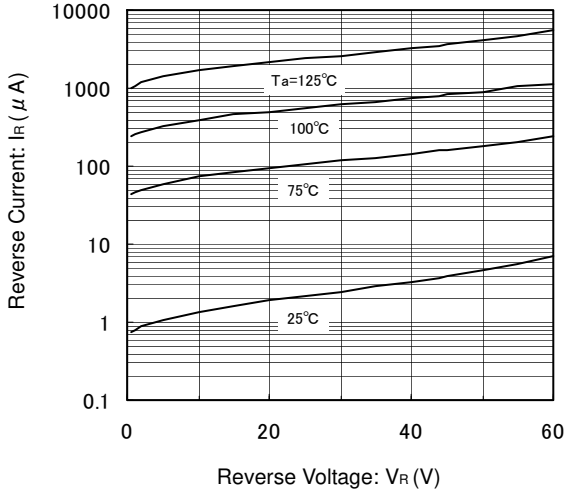


■TYPICAL PERFORMANCE CHARACTERISTICS

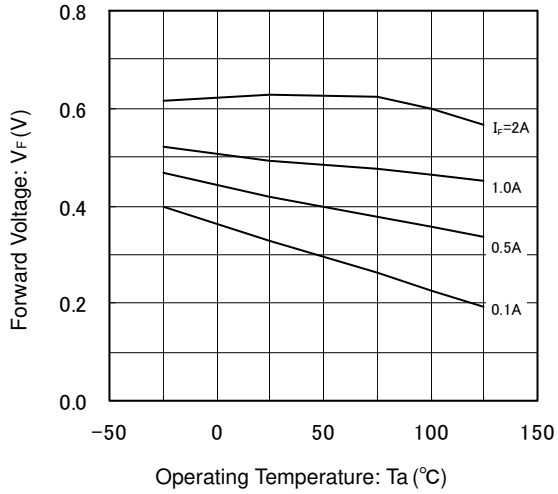
(1) Forward Current vs. Forward Voltage



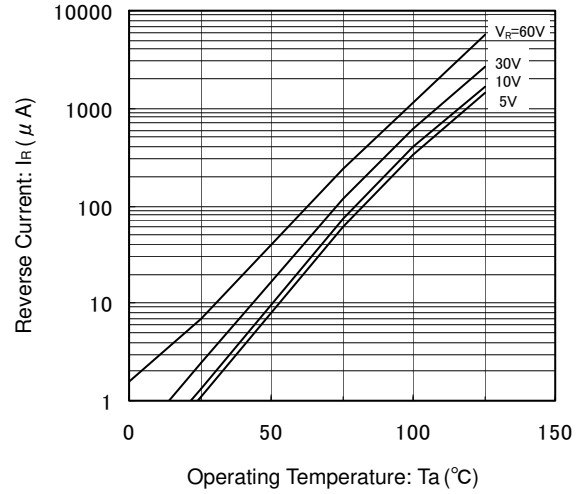
(2) Reverse Current vs. Reverse Voltage



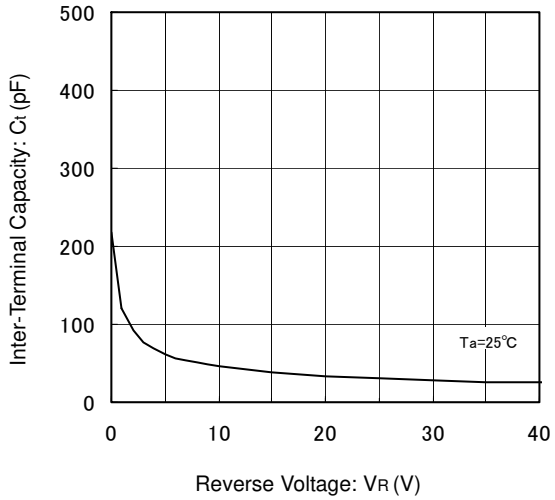
(3) Forward Voltage vs. Operating Temperature



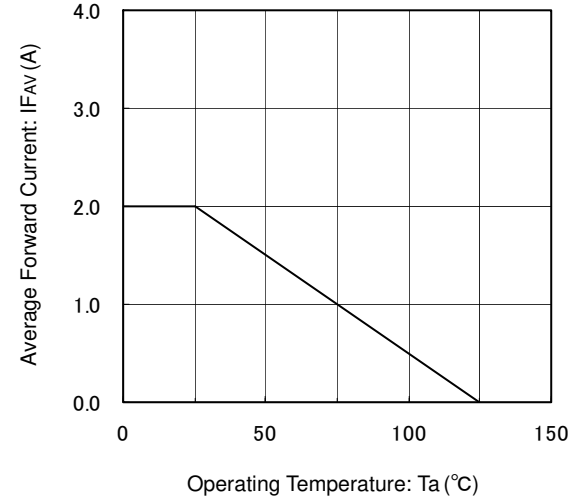
(4) Reverse Current vs. Operating Temperature



(5) Inter-Terminal Capacity vs. Reverse Voltage



(6) Average Forward Current vs. Operating Temperature



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